

**PRODUCT RELIABILITY REPORT
FOR**

DS2460, Rev A2

Dallas Semiconductor

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Prepared by:

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Conclusion

The following qualification successfully meets the quality and reliability standards required of all Dallas Semiconductor products:

DS2460, Rev A2

In addition, Dallas Semiconductor's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at <http://www.maxim-ic.com/TechSupport/dsreliability.html>.

Device Description:

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l_datasheet3.cfm.

Reliability Derating:

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

$$AfT = \exp((Ea/k)*(1/Tu - 1/Ts)) = tu/ts$$

AfT = Acceleration factor due to Temperature
tu = Time at use temperature (e.g. 55°C)
ts = Time at stress temperature (e.g. 125°C)
k = Boltzmann's Constant (8.617 x 10⁻⁵ eV/°K)
Tu = Temperature at Use (°K)
Ts = Temperature at Stress (°K)
Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

$$AfV = \exp(B*(Vs - Vu))$$

AfV = Acceleration factor due to Voltage
Vs = Stress Voltage (e.g. 7.0 volts)
Vu = Maximum Operating Voltage (e.g. 5.5 volts)
B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

$$Fr = X/(ts * AfV * AfT * N * 2)$$

X = Chi-Sq statistical upper limit
N = Life test sample size

Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

$$MTTF = 1/Fr$$

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE: MTTF (YRS): 46884 FITS: 2.4

The parameters used to calculate this failure rate are as follows:

Cf: 60% Ea: 0.7 B: 0 Tu: 25 °C Vu: 5.5 Volt

The reliability data follows. At the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available and may contain some generic data. "*" after DATE CODE denotes specific product

Device Information:

Process: D35WN-3P3M,DPE2,NTC,DSD,PDES,PDRES,Cap,ENPN
 Passivation: TopMetal 2 Mask NRL: TEOS Ox/Nitride
 Die Size: 70 x 100
 Number of Transistors: 62938
 Interconnect: Aluminum / 1% Silicon / 0.5% Copper
 Gate Oxide Thickness: 131 Å

ELECTRICAL CHARACTERIZATION

DESCRIPTION	DATE COD	CONDITION	READPOINT	QTY	FAILS	FA#
ESD SENSITIVITY	0509 *	EOS/ESD S5.1 HBM 500 VOLTS	1 PUL'S	3	0	
ESD SENSITIVITY	0509 *	EOS/ESD S5.1 HBM 1000 VOLTS	1 PUL'S	3	0	
ESD SENSITIVITY	0509 *	EOS/ESD S5.1 HBM 2000 VOLTS	1 PUL'S	3	0	
ESD SENSITIVITY	0509 *	EOS/ESD S5.1 HBM 4000 VOLTS	1 PUL'S	3	0	
ESD SENSITIVITY	0509 *	EOS/ESD S5.1 HBM 8000 VOLTS	1 PUL'S	3	0	
ESD SENSITIVITY	0509 *	IEC 61000-4-2 CONTACT 4000 VOLTS	10 PUL'S	3	0	
LATCH-UP	0509 *	JESD78, I-TEST 125C	2 DYS	6	0	
LATCH-UP	0509 *	JESD78, Vsupply TEST 125C	2 DYS	6	0	
Total:					0	

OPERATING LIFE

DESCRIPTION	DATE COD	CONDITION	READPOINT	QTY	FAILS	FA#
HIGH TEMP OP LIFE	0449	125C, 5.5 VOLTS	1000 HRS	45	0	
HIGH TEMP OP LIFE	0508	125C, 5.5 VOLTS	1000 HRS	77	0	
HIGH TEMP OP LIFE	0509 *	125C, 5.5 VOLTS	1000 HRS	77	0	
HIGH TEMP OP LIFE	0513	125C, 3.6 VOLTS	1000 HRS	72	0	
HIGH TEMP OP LIFE	0513	125C, 3.6 VOLTS	1000 HRS	45	0	

LOW TEMP OP LIFE	0523	25 C, 3.6 VOLTS	1000 HRS	72	0
HIGH TEMP REVERSE BIAS	0527	125C, 5.5 VOLTS	1000 HRS	83	0
Total:				0	0

W/E ENDURANCE AND DATA RET'N

DESCRIPTION	DATE COD	CONDITION	READPOINT	QTY	FAILS	FA#
STORAGE LIFE	0449	150C	1000 HRS	77	0	
WRITE CYCLE STRESS (KCYS)	0502	85 C, 3.5 VOLTS	10 KCYS	77	0	
STORAGE LIFE		150C	1000 HRS	77	0	
WRITE CYCLE STRESS (KCYS)	0502	25 C, 3.5 VOLTS	40 KCYS	77	0	
STORAGE LIFE		150C	1000 HRS	77	0	
WRITE CYCLE STRESS (KCYS)	0508	70 C, 5.5 VOLTS	30 KCYS	77	0	
STORAGE LIFE		150C	1000 HRS	75	0	
WRITE CYCLE STRESS (KCYS)	0509 *	85 C, 5.5 VOLTS	50 KCYS	77	1	30040981
STORAGE LIFE	*	150C	1000 HRS	74	0	
WRITE CYCLE STRESS (KCYS)	0513	70 C, 3.6 VOLTS	30 KCYS	67	0	
STORAGE LIFE		150C	1000 HRS	68	0	
WRITE CYCLE STRESS (CYS)	0540 *	25 C, 5.5 VOLTS	50 CYS	77	0	
STORAGE LIFE	*	150C	48 HRS	77	0	
WRITE CYCLE STRESS (KCYS)	*	85 C, 5.5 VOLTS	50 KCYS	77	0	
Total:				1	1	

FAILURE RATE: MTTF (YRS): 46884 FITS: 2.4

30040981 - Failure due to capacitor oxide defect at the poly1 to poly2 cap in the charge pump circuitry.